

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

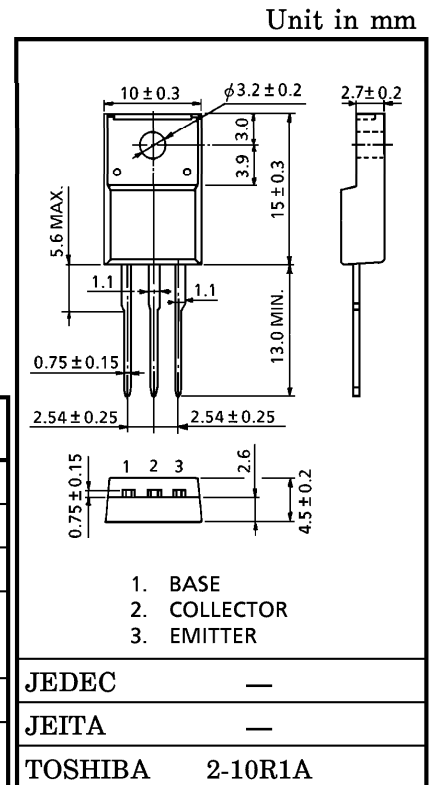
2SB1495

HIGH POWER SWITCHING APPLICATIONS

- High DC Current Gain
: $h_{FE} = 2000$ (Min.) ($V_{CE} = -2V, I_C = -2A$)
- Low Saturation Voltage
: $V_{CE(sat)} = -1.5V$ (MAX.) ($I_C = -1.5A$)
- Complementary to 2SD2257

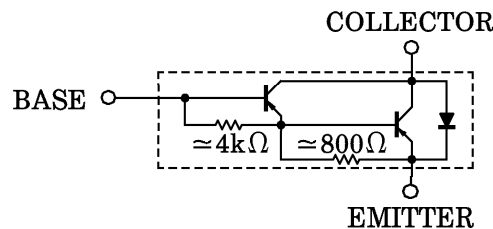
MAXIMUM RATINGS ($T_c = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	-100	V
Collector-Emitter Voltage		V_{CE0}	-100	V
Emitter-Base Voltage		V_{EB0}	-8	V
Collector Current	DC	I_C	-3	A
	Pulsed	I_{CP}	-5	
Base Current		I_B	-0.3	A
Collector Power Dissipation	$T_a = 25^\circ C$	P_C	2.0	W
	$T_c = 25^\circ C$		20	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$



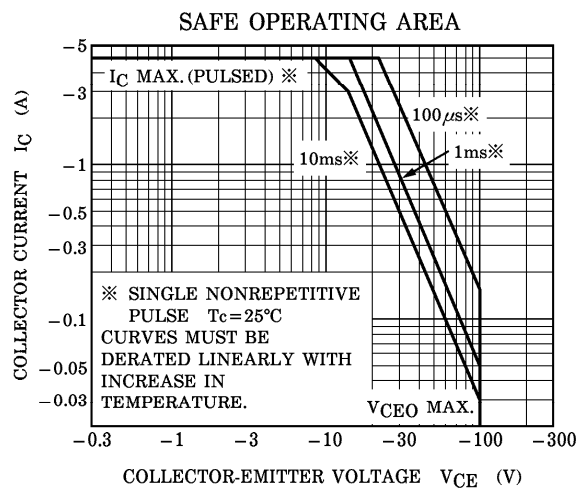
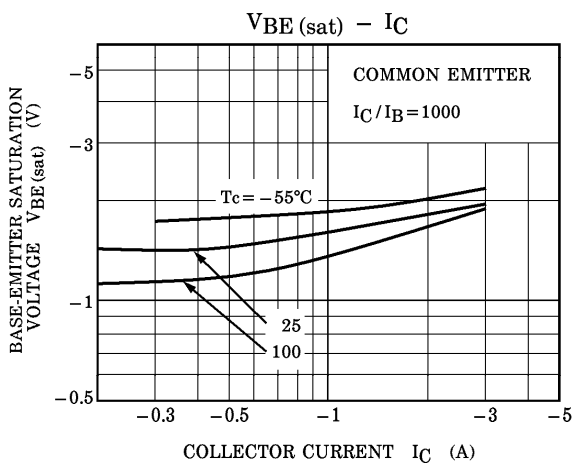
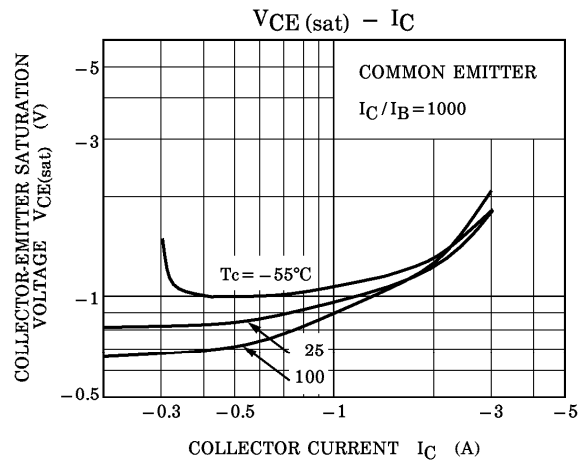
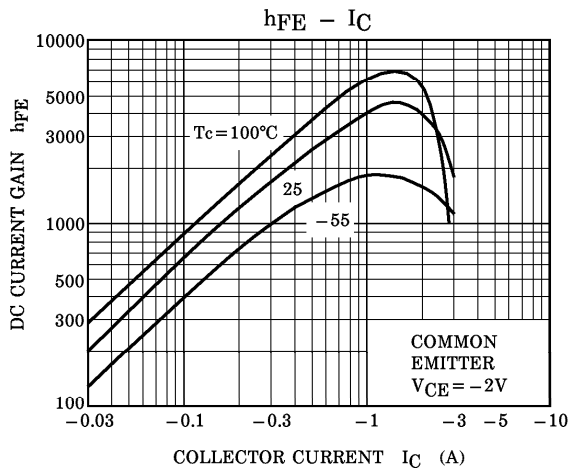
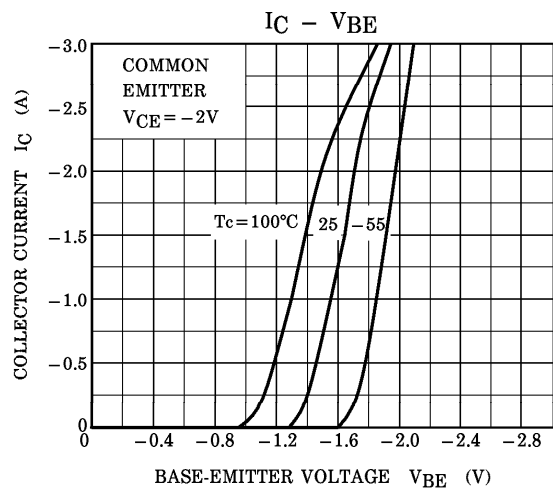
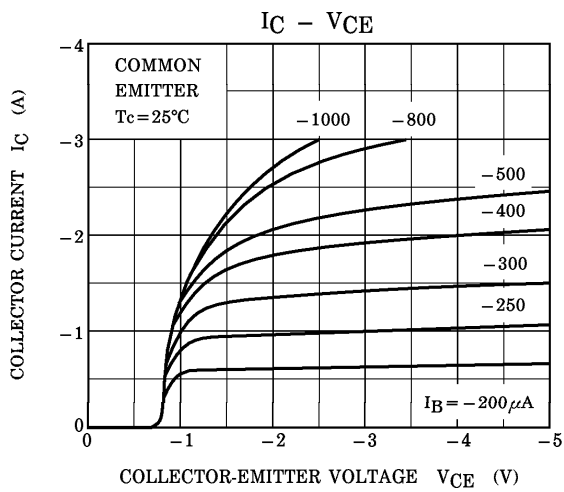
Weight : 1.7g (Typ.)

EQUIVALENT CIRCUIT



ELECTRICAL CHARACTERISTICS (T_c = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CB0}	V _{CB} = -100V, I _E = 0	—	—	-10	μA
Emitter Cut-off Current		I _{EB0}	V _{EB} = -8V, I _C = 0	-0.8	—	-4.0	mA
Collector-Emitter Breakdown Voltage		V _{(BR) CEO}	I _C = -10mA, I _B = 0	-100	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = -2V, I _C = -1A	2000	—	—	
		h _{FE} (2)	V _{CE} = -2V, I _C = -2A	2000	—	—	
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = -1.5A, I _B = -1.5mA	—	—	-1.5	V
Base-Emitter Saturation Voltage		V _{BE (sat)}	I _C = -1.5A, I _B = -1.5mA	—	—	-2.0	V
Switching Time	Turn-on Time	t _{on}	<p> $-I_{B1} = I_{B2} = 1.5\text{mA}$ DUTY CYCLE $\leq 1\%$ $V_{CC} = -30\text{V}$ </p>	—	0.5	—	μs
	Storage Time	t _{stg}		—	1.0	—	
	Fall Time	t _f		—	—	0.4	



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